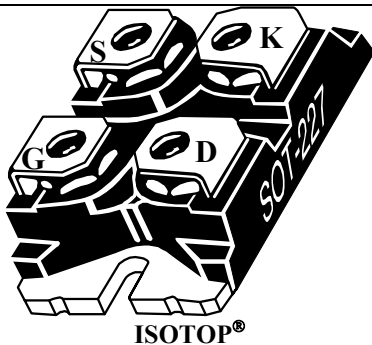
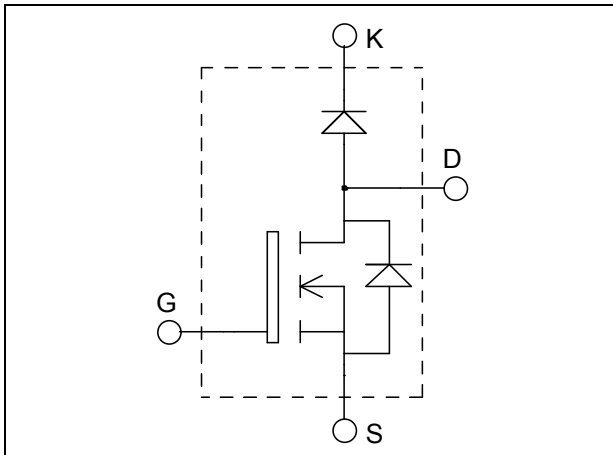


ISOTOP[®] Boost chopper Super Junction MOSFET Power Module

$V_{DSS} = 900V$
 $R_{DSon} = 120m\Omega \text{ max @ } T_j = 25^\circ C$
 $I_D = 33A \text{ @ } T_c = 25^\circ C$



Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- **COOLMOS**[★]
Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
- ISOTOP[®] Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_c of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	900	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	33
		$T_c = 80^\circ C$	25
I_{DM}	Pulsed Drain current	75	A
V_{GS}	Gate - Source Voltage	± 20	V
R_{DSon}	Drain - Source ON Resistance	120	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	290
I_{AR}	Avalanche current (repetitive and non repetitive)	8.8	A
E_{AR}	Repetitive Avalanche Energy	2.9	mJ
E_{AS}	Single Pulse Avalanche Energy	1940	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 900V$			100	μA
		$T_j = 25^\circ\text{C}$				
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 0V, V_{DS} = 900V$		500		$\text{m}\Omega$
		$T_j = 125^\circ\text{C}$				
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 3\text{mA}$	2.5	3	3.5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V; V_{DS} = 100V$		6.8		nF
C_{oss}	Output Capacitance	$f = 1\text{MHz}$		0.33		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 26A$		270		nC
Q_{gs}	Gate – Source Charge			32		
Q_{gd}	Gate – Drain Charge			115		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GS} = 10V$ $V_{Bus} = 600V$ $I_D = 26A$ $R_G = 7.5\Omega$		70		ns
T_r	Rise Time			20		
$T_{d(off)}$	Turn-off Delay Time			400		
T_f	Fall Time			25		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 10V; V_{Bus} = 600V$ $I_D = 26A; R_G = 7.5\Omega$		1.5		mJ
E_{off}	Turn-off Switching Energy			0.75		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 10V; V_{Bus} = 600V$ $I_D = 26A; R_G = 7.5\Omega$		2.1		mJ
E_{off}	Turn-off Switching Energy			0.85		

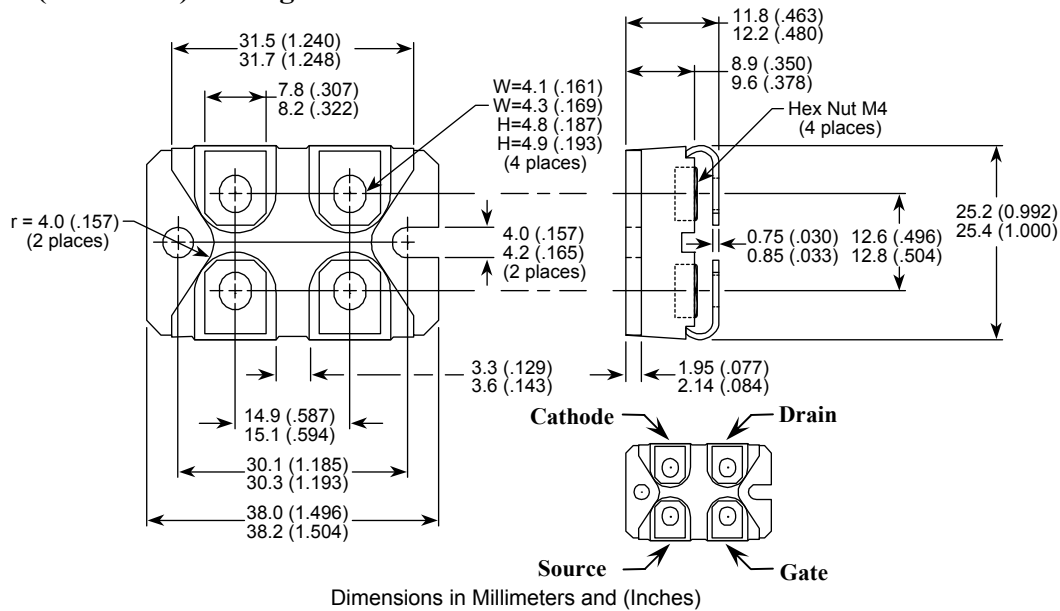
Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$		100	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current	$T_c = 80^\circ\text{C}$		30		A
V_F	Diode Forward Voltage	$I_F = 30A$		2.6	3.1	V
		$I_F = 60A$		3.2		
		$I_F = 30A$	$T_j = 125^\circ\text{C}$	1.8		
t_{rr}	Reverse Recovery Time	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	300		ns
			$T_j = 125^\circ\text{C}$	380		
Q_{rr}	Reverse Recovery Charge	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	360		nC
			$T_j = 125^\circ\text{C}$	1700		

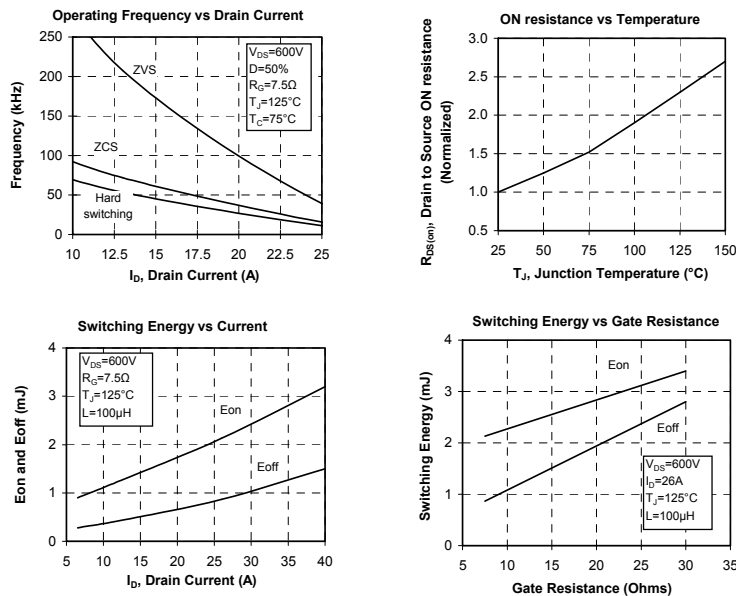
Thermal and package characteristics

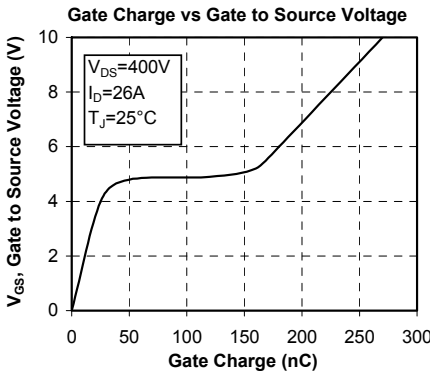
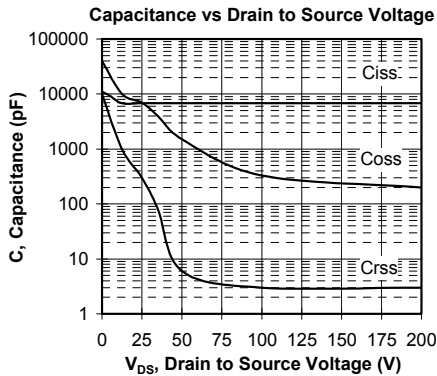
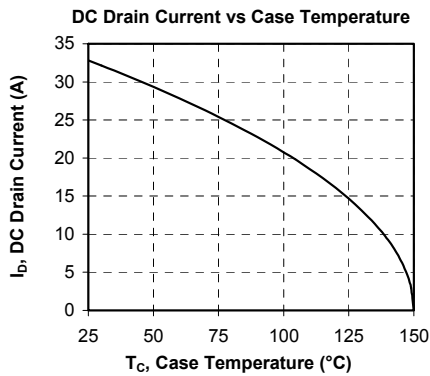
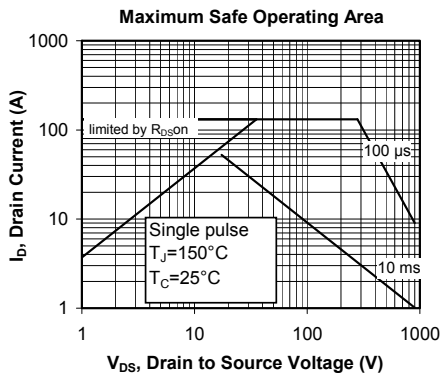
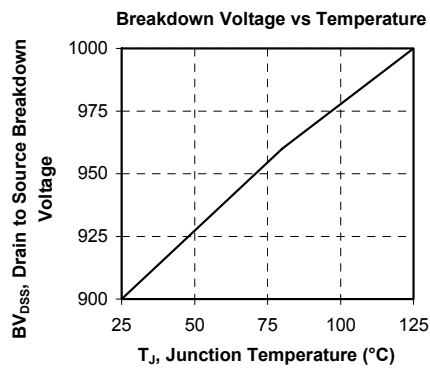
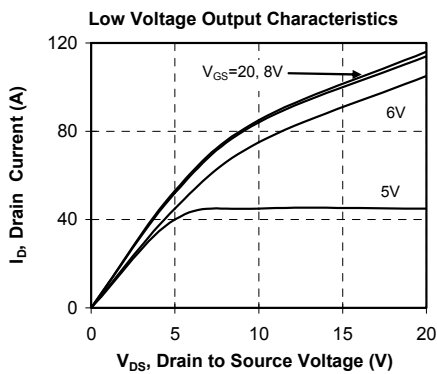
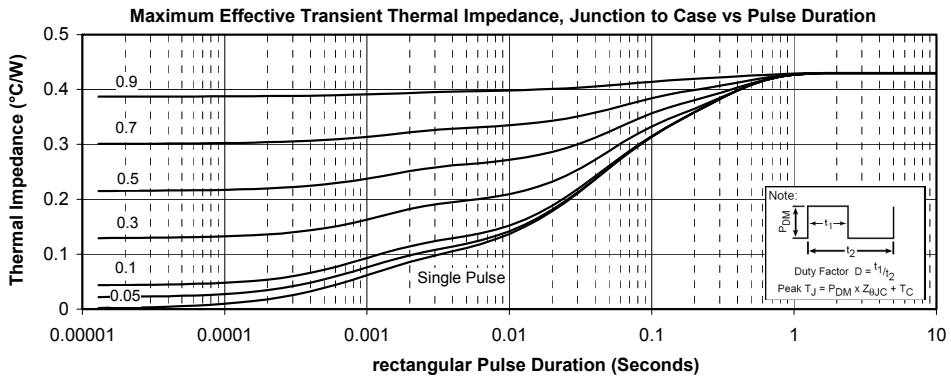
Symbol	Characteristic	Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	CoolMOS		0.43	°C/W
		Diode		1.05	
R _{thJA}	Junction to Ambient (IGBT & Diode)			20	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	2500			V
T _J , T _{STG}	Storage Temperature Range	-40		150	°C
T _L	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

SOT-227 (ISOTOP[®]) Package Outline

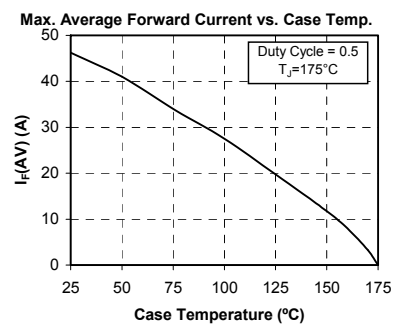
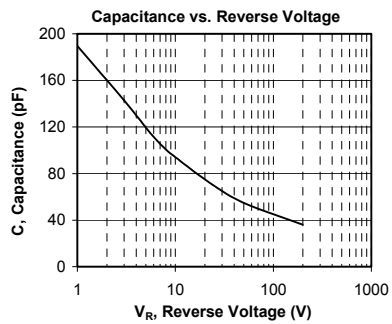
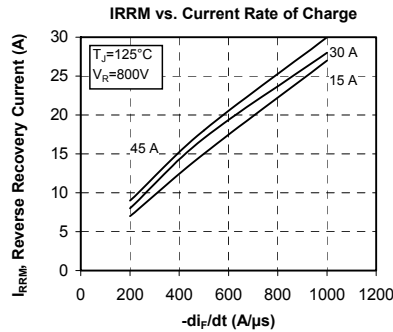
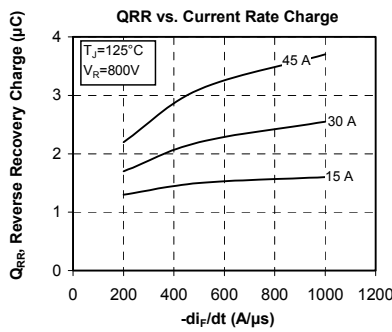
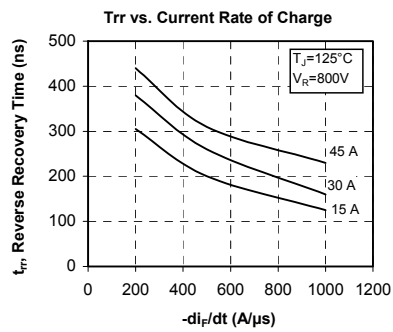
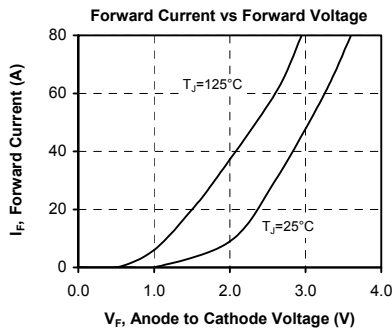
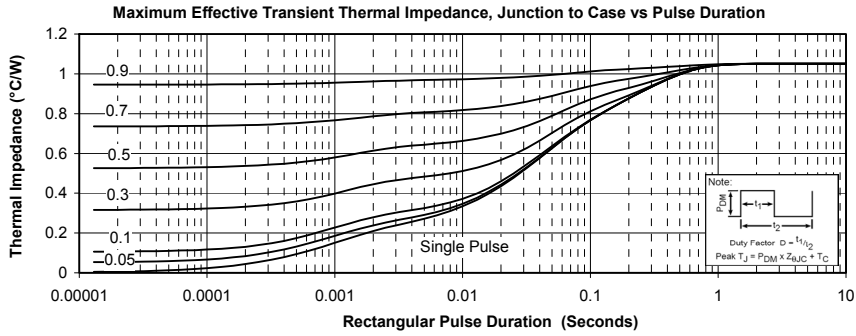


Typical CoolMOS performance Curve





Typical Chopper diode performance Curve



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[25.330.4753.1](#) [25.330.5253.1](#) [25.334.3253.1](#) [25.334.3353.1](#) [25.350.2053.0](#) [25.352.4753.1](#) [25.522.3253.0](#) [T483C](#) [T484C](#) [T485F](#) [T485H](#)
[T512F-YEB](#) [T513F](#) [T514F](#) [T554](#) [T612FSE](#) [25.161.3453.0](#) [25.179.2253.0](#) [25.194.3253.0](#) [25.325.1253.1](#) [25.326.4253.1](#) [25.330.0953.1](#)
[25.332.4353.1](#) [25.350.1653.0](#) [25.350.2453.0](#) [25.352.1453.0](#) [25.352.1653.0](#) [25.352.2453.0](#) [25.352.5453.1](#) [25.522.3353.0](#) [25.602.4053.0](#)
[25.640.5053.0](#)